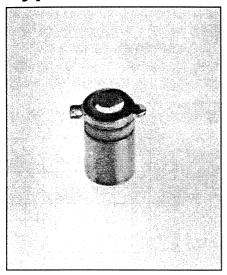
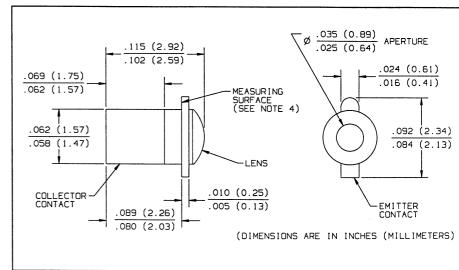


## **PN Junction Silicon Photodiode** Type OP900SL





#### **Features**

- · Narrow receiving angle
- Enhanced temperature range
- Ideal for direct mounting in PC boards
- Fast switching speed
- Mechanically and spectrally matched to the OP123 series emitters
- Linear response vs. irradiance

#### Description

The OP900SL consists of a PN junction silicon photodiode mounted in a miniature, glass lensed, hermetically sealed "Pill" package. The lensing effect allows an acceptance half angle of 18° measured from the optical axis to the half power point.

### Replaces

OP900 series

## **Absolute Maximum Ratings** (T<sub>A</sub> = 25° C unless otherwise noted)

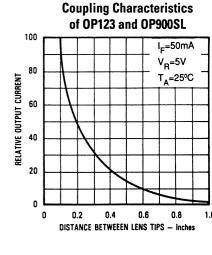
| Reverse Voltage                                    |
|--|
| Storage Temperature Range65° C to +150°            |
| Operating Temperature Range65° C to +125°          |
| Soldering Temperature (5 sec. with soldering iron) |
| Power Dissipation                                  |
| Notoc  |

- (1) RMA flux is recommended. Duration can be extended to 10 sec. max. when flow soldering. (2) Derate linearly 0.5 mW/° C above 25° C.
- (3) Junction temperature maintained at 25° C.
- (4) Light source is an unfiltered tungsten bulb operating at CT = 2870 K or equivalent infrared source.

### **Typical Performance Curves**

## 100 % 80 Relative Response 60 600 700 800 900 1000 Wavelength - nm

**Typical Spectral Response** 

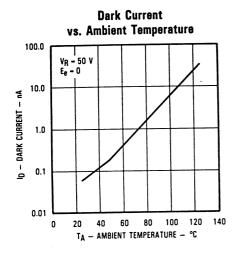


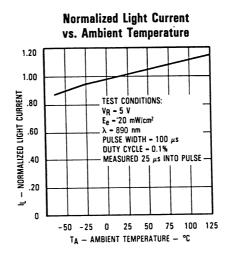
# Type OP900SL

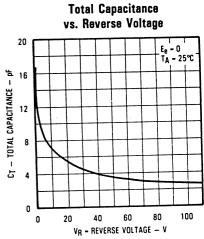
Electrical Characteristics (T<sub>A</sub> = 25° C unless otherwise noted)

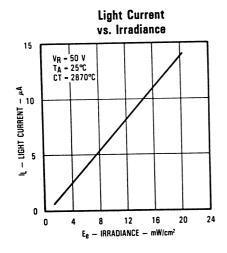
| SYMBOL         | PARAMETER                 | MIN | TYP        | MAX | UNITS    | TEST CONDITIONS   |
|----------------|---------------------------|-----|------------|-----|----------|---|
| I <sub>L</sub> | Light Current             | 8.0 | 14.0       |     | μА       | $V_R = 10 \text{ V}, E_e = 20 \text{ mW/cm}^{2(3)(4)}$                                    |
| I <sub>D</sub> | Dark Current              | -   |            | 10  | nA       | $V_R = 10 \text{ V}, E_e = 0^{(3)}$   |
|                | Reverse Voltage Breakdown | 100 | 150        |     | V        | I <sub>R</sub> = 100 μA   |
| t <sub>r</sub> | Rise Time<br>Fall Time    |     | 100<br>100 |     | ns<br>ns | $V_R = 50 \text{ V}, I_L = 8 \mu\text{A}$<br>$R_L = 1 \text{ k}\Omega$ , See Test Circuit |

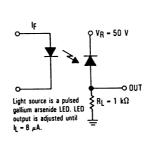
## **Typical Performance Curves**











**Switching Time** 

**Test Circuit** 

